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Kind regards,

Team Nexperia

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier in common cathode configuration with an integrated guard ring for stress protection, encapsulated in an ultra thin DFN2020D-3 (SOT1061D) leadless small Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

2. Features and benefits

- Average forward current I_{F(AV)} ≤ 2 A
- Reverse voltage V_R ≤ 20 V
- Low forward voltage V_F ≤ 420 mV
- Low reverse current
- Reduced Printed-Circuit-Board (PCB) area requirements
- Exposed heat sink (cathode pad) for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with visible and solderable side pads
- · Suitable for Automatic Optical Inspection (AOI) of solder joints
- AEC-Q101 qualified

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Free-wheeling application
- Reverse polarity protection
- Low power consumption application
- Battery chargers for mobile equipment
- LED backlight for mobile application

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per diode							
I _{F(AV)}	average forward current	δ = 0.5; f = 20 kHz; $T_{amb} \le 80$ °C; square wave	[1]	-	-	2	Α
		δ = 0.5; f = 20 kHz; $T_{sp} \le$ 140 °C; square wave		-	-	2	Α





Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _R	reverse voltage	T _j = 25 °C		-	-	20	V
Per diode							
V _F	forward voltage	I_F = 2 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed		-	385	420	mV
I _R	reverse current	$V_R = 20 \text{ V; } t_p \le 300 \mu\text{s; } \delta \le 0.02;$ $T_j = 25 \text{ °C; pulsed}$		-	380	1000	μA

^[1] Device mounted on a ceramic PCB, Al_2O_3 , standard footprint.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	anode diode 1	A1	3	3
2	anode diode 2	A2		* *
3	common cathode	К	Transparent top view DFN2020D-3 (SOT1061D)	1 2 006aaa438

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMEG2020CPAS	DFN2020D-3	DFN2020D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm	SOT1061D		

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG2020CPAS	CW

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per diode						
V _R	reverse voltage	T _j = 25 °C		-	20	V
l _F	forward current	T _{sp} ≤ 135 °C; δ = 1		-	2.8	Α
I _{F(AV)}	average forward current	δ = 0.5; f = 20 kHz; $T_{amb} \le 80$ °C; square wave	[1]	-	2	Α
		δ = 0.5; f = 20 kHz; $T_{sp} \le$ 140 °C; square wave		-	2	A
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ ms}; \ \delta \le 0.25$		-	7	Α
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	9	Α
Per device;	one diode loaded					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	500	mW
			[3]	-	960	mW
			[1]	-	1800	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

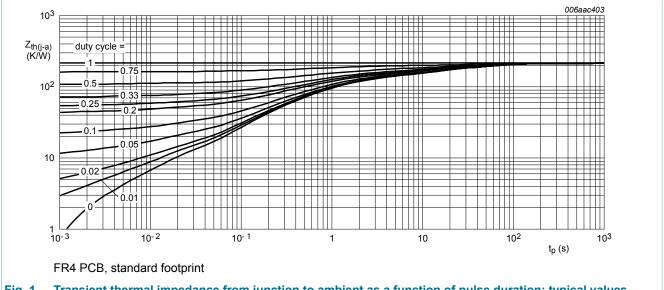
Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

Thermal characteristics

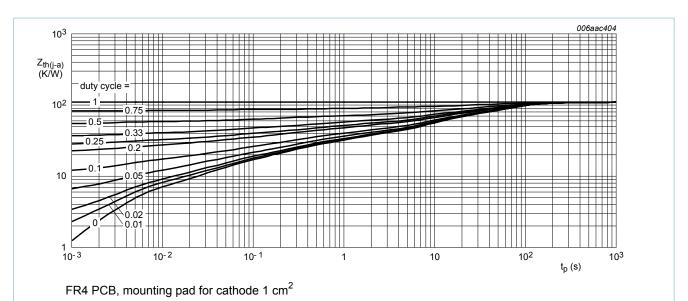
Thermal characteristics Table 6.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per device; one diode loaded							
R _{th(j-a)} thermal resistance		in free air [1]	[1][2]	-	-	250	K/W
	from junction to ambient		[1][3]	-	-	130	K/W
	ambient		[1][4]	-	-	70	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	12	K/W

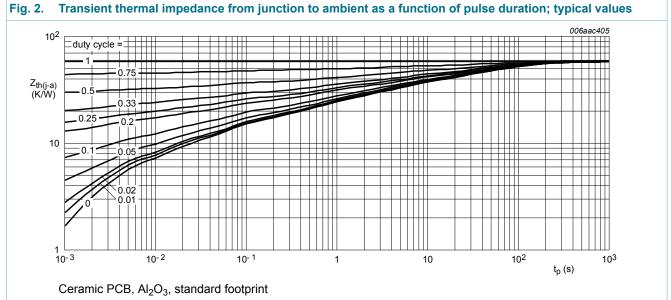
- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- Device mounted on a ceramic PCB, Al₂O₃, standard footprint. [4]
- Soldering point of cathode tab. [5]



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

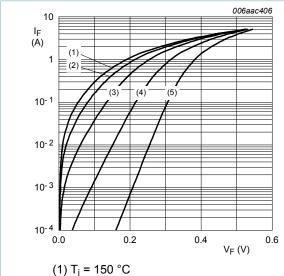


Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 3.

10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
$V_{(BR)R}$	reverse breakdown voltage	I_R = 5 mA; T_j = 25 °C; t_p = 300 μs; $δ$ = 0.02; pulsed	20	-	-	V
V _F forward voltage	forward voltage	I_F = 100 mA; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed	-	220	-	mV
		I_F = 1 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed	-	320	360	mV
		I_F = 2 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed	-	385	420	mV
I _R reverse current	reverse current	$V_R = 10 \text{ V}; t_p \le 300 \mu\text{s}; \delta \le 0.02;$ $T_j = 25 ^{\circ}\text{C}; \text{ pulsed}$	-	160	-	μA
		$V_R = 20 \text{ V; } t_p \le 300 \mu\text{s; } \delta \le 0.02;$ $T_j = 25 \text{ °C; pulsed}$	-	380	1000	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	175	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	65	-	pF
t _{rr}	reverse recovery time	I_F = 10 mA; I_R = 10 mA; R_L = 100 Ω; $I_{R(meas)}$ = 1 mA; T_j = 25 °C	-	55	-	ns





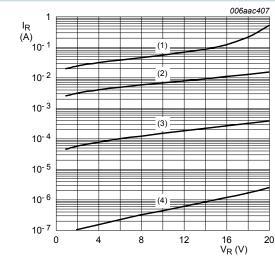
⁽²⁾ $T_i = 125 \, ^{\circ}C$

(3)
$$T_i = 85 \, ^{\circ}C$$

(4)
$$T_i = 25 \,^{\circ}C$$

(5)
$$T_i = -40 \, ^{\circ}\text{C}$$

Forward current as a function of forward voltage; typical values



(1) $T_i = 125 \, ^{\circ}C$

(2)
$$T_i = 85 \, ^{\circ}C$$

(3)
$$T_i = 25 \,^{\circ}C$$

(4)
$$T_j = -40 \, ^{\circ}C$$

Reverse current as a function of reverse voltage; typical values

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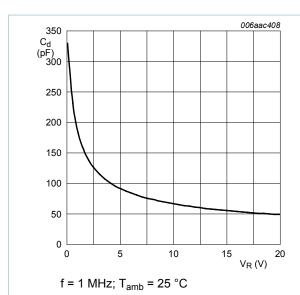
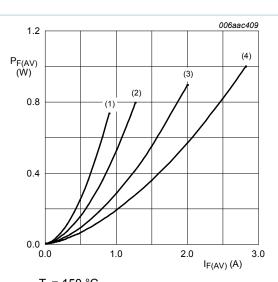


Fig. 6. Diode capacitance as a function of reverse voltage; typical values

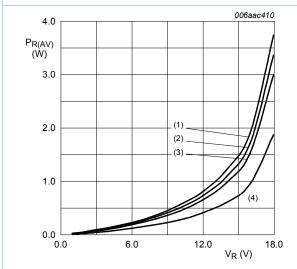


 $T_j = 150 \,^{\circ}\text{C}$ (1) $\delta = 0.1$ (2) $\delta = 0.2$

 $(3) \delta = 0.5$

 $(4) \delta = 1$

Fig. 7. Average forward power dissipation as a function of average forward current; typical values

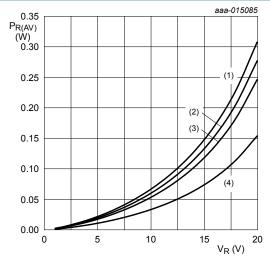


 $T_j = 125 \,^{\circ}\text{C}$ (1) $\delta = 1$

 $(2) \delta = 0.9$

 $(3) \delta = 0.8$ $(4) \delta = 0.5$

Average reverse power dissipation as a function of reverse voltage; typical values



T_j = 85 °C

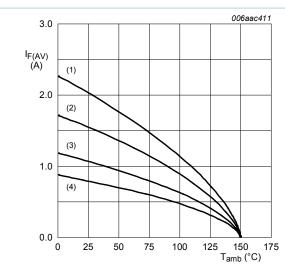
 $(1) \delta = 1$

 $(2) \delta = 0.9$

 $(3) \delta = 0.8$ $(4) \delta = 0.5$

Fig. 9. Average reverse power dissipation as a function of reverse voltage; typical values

Fig. 8.



FR4 PCB, standard footprint

T_i = 150 °C

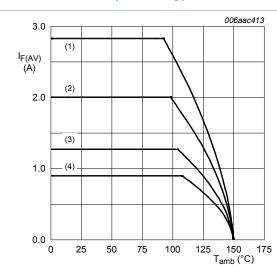
(1) δ = 1; DC

(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

T_i = 150 °C

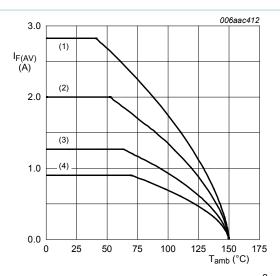
(1) $\delta = 1$; DC

(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 12. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm²

T_i = 150 °C

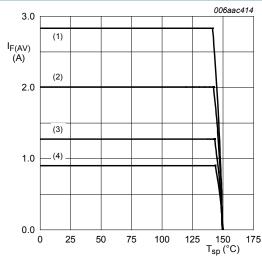
(1) δ = 1; DC

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values



T_i = 150 °C

(1) δ = 1; DC

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 13. Average forward current as a function of solder point temperature; typical values

11. Test information

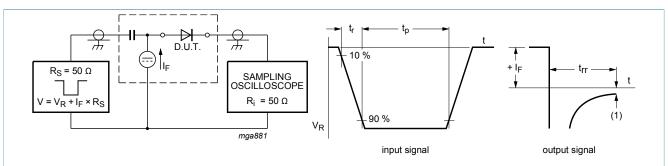


Fig. 14. Reverse recovery time: test circuit and waveforms

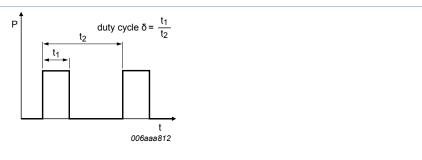


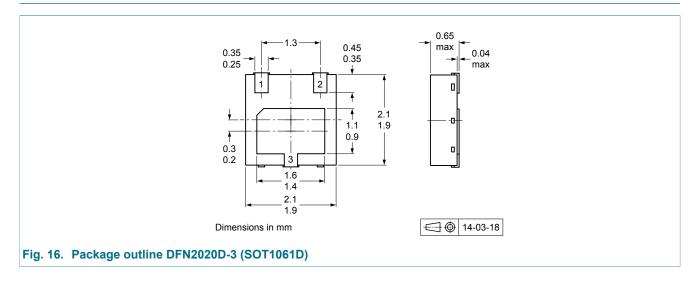
Fig. 15. Duty cycle definition

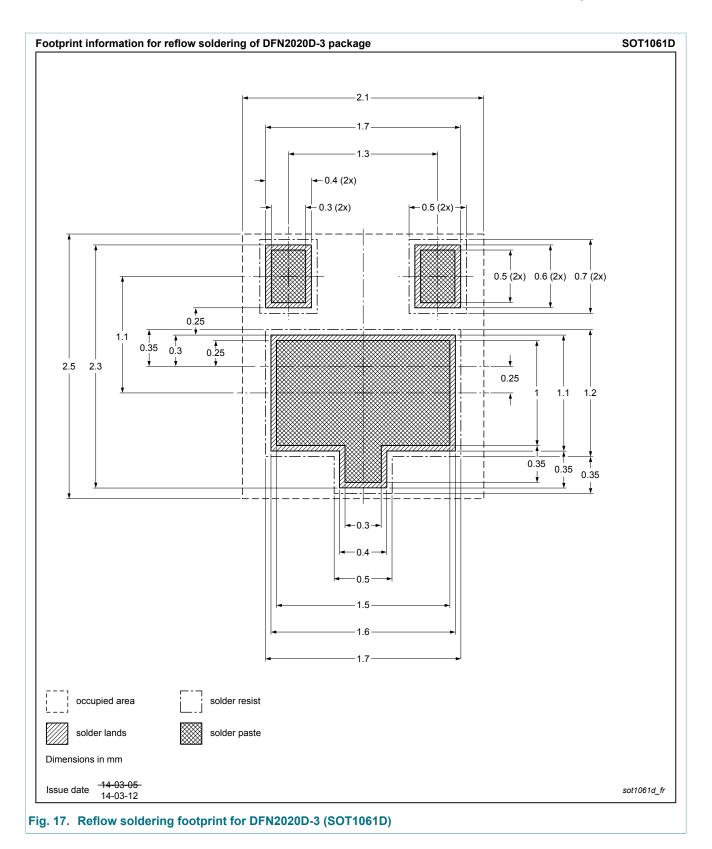
The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline





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13. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMEG2020CPAS v.2	20150120	Product data sheet	-	PMEG2020CPAS v.1			
Modifications:	changed data sheet	changed data sheet status					
PMEG2020CPAS v.1	20141210	Preliminary data sheet	-	-			

14. Legal information

14.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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